

2SK1835

Silicon N Channel MOS FET

REJ03G0978-0400 Rev.4.00 Jun 04, 2008

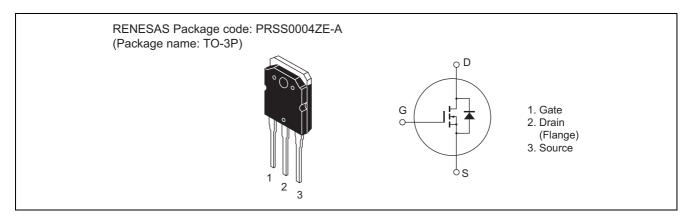
Application

High speed power switching

Features

- High breakdown voltage ($V_{DSS} = 1500 \text{ V}$)
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	1500	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	4	Α
Drain peak current	I _{D(pulse)} Note1	10	Α
Body to drain diode reverse drain current	I _{DR}	4	Α
Channel dissipation	Pch Note2	125	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1 %

2. Value at Tc = 25°C

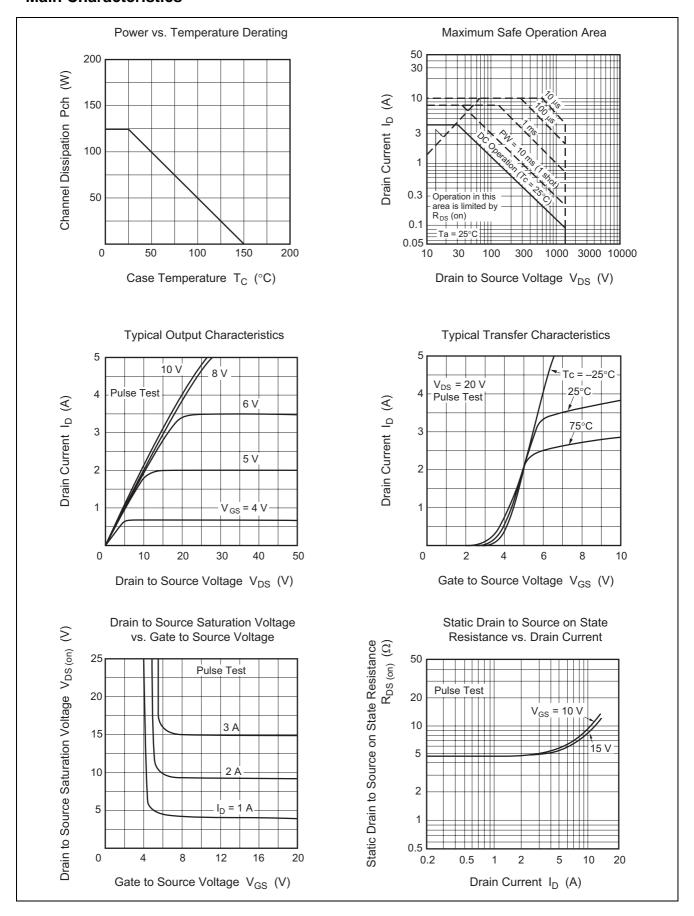
Electrical Characteristics

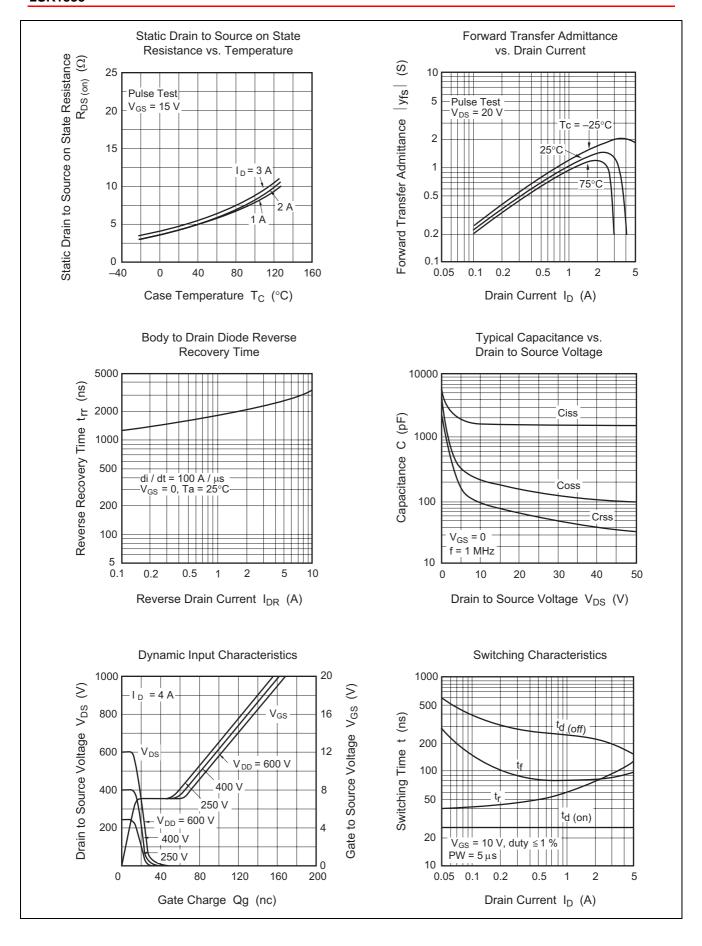
 $(Ta = 25^{\circ}C)$

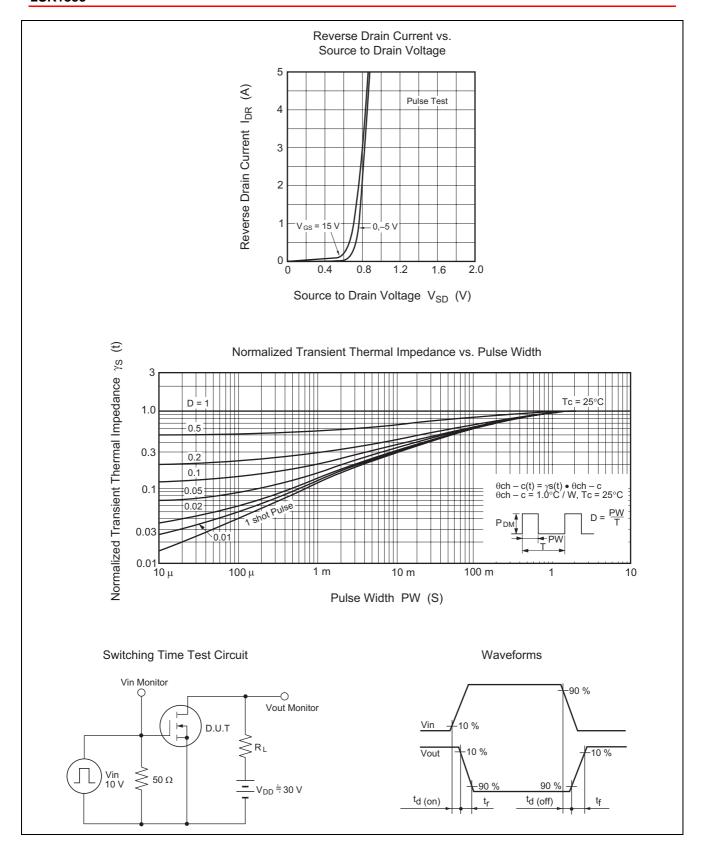
Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	1500	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±1	μΑ	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	500	μΑ	V _{DS} = 1200 V, V _{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	_	4.0	V	$I_D = 1 \text{ mA}, V_{DS} = 10 \text{ V}$
Static drain to source on state	R _{DS(on)}	_	4.6	7.0	Ω	$I_D = 2 \text{ A}, V_{GS} = 15 \text{ V}^{\text{Note 3}}$
resistance						
Forward transfer admittance	y _{fs}	0.9	1.4	_	S	$I_D = 2 \text{ A}, V_{DS} = 20 \text{ V}^{\text{Note 3}}$
Input capacitance	Ciss	_	1700	_	pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	230	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	100	_	pF	
Turn-on delay time	t _{d(on)}	_	25	_	ns	$I_D = 2A, V_{GS} = 10 V,$
Rise time	t _r	_	80	_	ns	$R_L = 15 \Omega$
Turn-off delay time	t _{d(off)}	_	230	_	ns	
Fall time	t _f	_	80	_	ns	
Body to drain diode forward voltage	V_{DF}	_	0.85	_	V	$I_F = 4 A, V_{GS} = 0$
Body to drain diode reverse	t _{rr}	_	2500	_	ns	$I_F = 4 A, V_{GS} = 0,$
recovery time						$di_F/dt = 100 A/\mu s$

Note: 3. Pulse Test

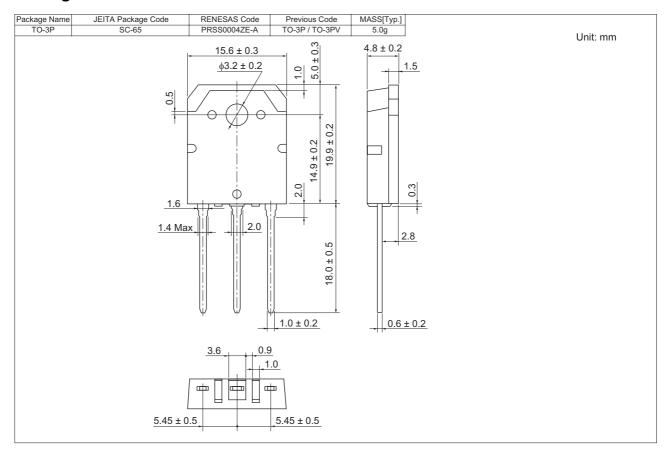
Main Characteristics







Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK1835-E	360 pcs	Box (Tube)

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- Renesas lechnology Corp. Sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan Notes:

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